# 2SK1339

Silicon N-Channel MOS FET

# HITACHI

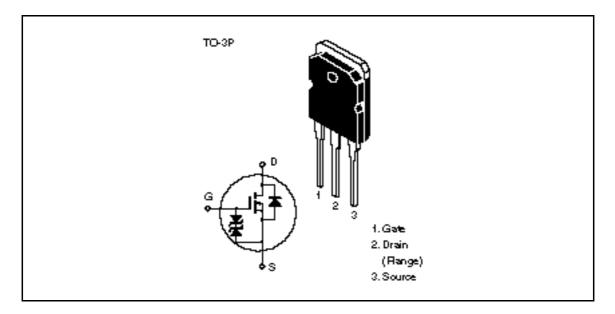
#### Application

High speed power switching

#### Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

#### Outline





# 2SK1339

# Absolute Maximum Ratings (Ta = $25^{\circ}$ C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	900	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	3	А
Drain peak current	I D(pulse) * 1	7	А
Body to drain diode reverse drain current	I <sub>DR</sub>	3	А
Channel dissipation	Pch*2	80	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW 10 µs, duty cycle 1%

2. Value at  $T_c = 25^{\circ}C$ 

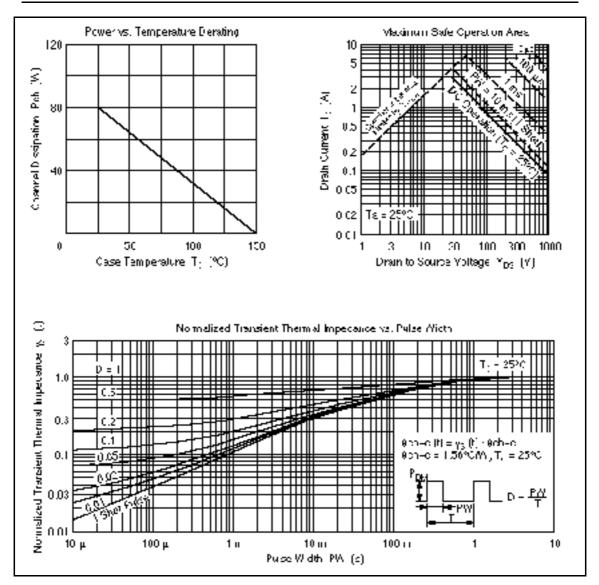
# **Electrical Characteristics** (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	900	_	_	V	$I_{\rm D} = 10$ mA, $V_{\rm GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	250	μΑ	$V_{\rm DS} = 720 \ V, \ V_{\rm GS} = 0$
Gate to source cutoff voltage	$V_{\text{GS(off)}}$	2.0	_	3.0	V	$I_{\rm D} = 1 \text{ mA}, V_{\rm DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{\text{DS(on)}}$	_	5.0	7.0		$I_{\rm D}$ = 1.5 A, $V_{\rm GS}$ = 10 V * <sup>1</sup>
Forward transfer admittance	yfs	1.2	1.9	_	S	$I_{\rm D}$ = 1.5 A, $V_{\rm DS}$ = 20 V * <sup>1</sup>
Input capacitance	Ciss	—	425	_	pF	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0,$
Output capacitance	Coss	_	175	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	85	_	pF	_
Turn-on delay time	t <sub>d(on)</sub>	_	10	_	ns	$I_{\rm D} = 2 \text{ A}, \text{ V}_{\rm GS} = 10 \text{ V},$
Rise time	t,	_	40	_	ns	
Turn-off delay time	$t_{d(off)}$	_	50	_	ns	_
Fall time	t <sub>f</sub>	_	55	_	ns	_
Body to drain diode forward voltage	$V_{DF}$	_	0.9	_	V	$I_{F} = 3 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t <sub>rr</sub>		850	_	ns	$I_F = 3 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A}/\mu\text{s}$
Note: 1 Pulse test						

Note: 1. Pulse test

See characteristic curves of 2SK1338.

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Hitachi, Ltd.

Semiconductor & IC DV. Neppon Bidg, 2-5-2, Ohte-mach, Chiyoda-ku, Tokyo 100, Japan Tet Tokyo (03, 3270-2111 Fax (03, 3270-5109

For Author in forms ion write to : Hischi America, Utd Semiconductor & IC DV. 2000 Sierra Point Parkway Briebana, CA. 94005-4835 U S.A. Tet 415-583-4207

Hitschi Burope GmbH Bectronic Components Group Cratinertel Burope Danecher Streße 3 D-85522 Feldkirchen Minchen Tet 089-9 94 80-0 Fex: 089-9 29 30 00 Hitschi Europe Ltd. Bedtonic Components Div. Northern Burge Hesdguerters Whitebrook Park Lower Cook hem Road Meidenhesd Berkshire SLGSYA Urited Kingdom Tet 0528-585000 Fex 0528-778322 Hitschi Asia Pta. Ltd 45 Collyer Quay \$20-00 Hitschi Towar Singspore 0404 Tet 535-2400 Fex 535-4533

Hischi Asia (Hong Kong) Ltd. Unit 705, North Towar, World Finance Cantre, Herbour City, Carton Road Taim She Taui, Kowloon Hang Kong Tet 27:359218 Fax: 27:35607.4

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